

EAST Search History

EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2	("20020130106" "20030084925").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2009/11/04 11:27
L2	1	1 and (revolution\$1 rpm\$1 "r.p.m.")	US-PGPUB; USPAT; USOCR	OR	ON	2009/11/04 11:28
L3	1	"20070131256".pn.	US-PGPUB; USPAT; USOCR	OR	ON	2009/11/04 11:55
L4	1	3 and (hydrophobic hydrophilic)	US-PGPUB; USPAT; USOCR	OR	ON	2009/11/04 11:55
L5	2	1 and (hydrophobic hydrophilic "si. sub.s" "si" silicon "silicon-dioxide")	US-PGPUB; USPAT; USOCR	OR	ON	2009/11/04 11:58
L6	1	"5271774".PN.	US-PGPUB; USPAT; USOCR	OR	ON	2009/11/04 12:02
L7	1	"20080173333".pn.	US-PGPUB; USPAT; USOCR	OR	ON	2009/11/04 12:21
L8	1	7 and ("pure-water" water aqueous)	US-PGPUB; USPAT; USOCR	OR	ON	2009/11/04 12:21
S1	1	"20070131256".pn.	US-PGPUB; USPAT; USOCR	OR	ON	2009/11/02 12:23
S2	1	("5997653").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2009/11/02 12:24
S4	2	("20020130106" "20030084925").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2009/11/02 12:34
S5	3	("NANBA, HIROMITSU" "YABUTA, TAKASHI" "ORII, TAKEHIKO").in. and ((substrate\$1 wafer\$1 semiconductor \$1 workpiece\$1) and (clean\$4 treat \$4 wash\$3) and (rins\$3 water) and (spin\$4 rotat\$3) and dry\$3 and (film \$1 layer\$1)).clm.	US-PGPUB; USPAT; USOCR	OR	ON	2009/11/02 12:46
S6	16	("TOKYO ELECTRON LIMITED").as. and ((substrate\$1 wafer\$1 semiconductor\$1 workpiece\$1) and (clean\$4 treat\$4 wash\$3) and (rins \$3 water) and (spin\$4 rotat\$3) and dry\$3 and (film\$1 layer\$1)).clm.	US-PGPUB; USPAT; USOCR	OR	ON	2009/11/02 12:54
S7	1	"20070131256".pn.	US-PGPUB; USPAT; USOCR	OR	ON	2009/11/02 16:05
S8	1	("5997653").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2009/11/02 16:05
S9	2	("20020130106" "20030084925").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2009/11/02 16:05

S10	16	("TOKYO ELECTRON LIMITED").as. and ((substrate\$1 wafer\$1 semiconductor\$1 workpiece\$1) and (clean\$4 treat\$4 wash\$3) and (rins \$3 water) and (spin\$4 rotat\$3) and dry\$3 and (film\$1 layer\$1)).clm.	US-PGPUB; USPAT; USOCR	OR	ON	2009/11/02 16:05
S11	7120	(substrate\$1 wafer\$1 semiconductor \$1 workpiece\$1) and (clean\$4 treat \$4 wash\$3) and ((rins\$3 "pure- water" water) same (mov\$3 advanc \$3 cross\$3 go goes going migrat\$3) same (out outward edge circumference)) and (((spin\$4 rotat \$3) and dry\$3) spin-dry\$3) and (film \$1 layer\$1)	US-PGPUB; USPAT	OR	ON	2009/11/02 16:23
S12	363	S11 and ((substrate\$1 wafer\$1 semiconductor\$1 workpiece\$1) same (clean\$4 treat\$4 wash\$3)) and ((rins \$3 "pure-water" water) with (mov\$3 advanc\$3 cross\$3 go goes going migrat\$3) with (out outward edge circumference)) and (((spin\$4 rotat \$3) and dry\$3) spin-dry\$3) same (film\$1 layer\$1))	US-PGPUB; USPAT	OR	ON	2009/11/02 16:25
S13	2353	(substrate wafer semiconductor workpiece) and (clean cleaning treat treating treatment wash washing) and ((rinse rinsing "pure-water" water) same (move moves moving moved advance advances advancing advanced cross crosses crossing across go goes going migrate migrating migrates migration) same (out outward edge circumference)) and (((spin spinning spun rotate rotation rotated rotating) and dry drying dried) "spin-dry" "spin-drying" "spin-dries") and (film layer)	USOCR	OR	ON	2009/11/02 16:28
S14	978	S13 and (nitrogen "n.sub.2")	USOCR	OR	ON	2009/11/02 16:29
S15	1343	S8 S9 S12 S14	US-PGPUB; USPAT; USOCR	OR	ON	2009/11/02 16:31
S16	120	S15 and "134".clas.	US-PGPUB; USPAT; USOCR	OR	ON	2009/11/02 16:31
S17	44	S16 and 134/33,94.1,95.2,137,149. ccls.	US-PGPUB; USPAT; USOCR	OR	ON	2009/11/02 16:32

S18	2	(S8 S9) and (substrate wafer semiconductor workpiece) and (clean cleaning treat treating treatment wash washing) and ((rinse rinsing "pure-water" water) same (move moves moving moved advance advances advancing advanced cross crosses crossing across go goes going migrate migrating migrates migration) same (out outward edge circumference)) and (((spin spinning spun rotate rotation rotated rotating) and dry drying dried) "spin-dry" "spin-drying" "spin-dries") and (film layer)	US-PGPUB; USPAT; USOCR	OR	ON	2009/11/02 16:34
S19	14	(substrate\$1 wafer\$1 semiconductor \$1 workpiece\$1) and (clean\$4 treat \$4 wash\$3) and ((rins\$3 "pure-water" water) same (mov\$3 advanc \$3 cross\$3 go goes going migrat\$3) same (out outward edge circumference)) and (((spin\$4 rotat \$3) and dry\$3) spin-dry\$3) and (film \$1 layer\$1)	FPRS; EPO; JPO; DERWENT	OR	ON	2009/11/02 16:34
S20	2	("20020130106" "20030084925").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2009/11/03 10:53
S21	2	S20 and (reduc\$3 less lessen\$3 slow \$3 stop stopp\$3 off)	US-PGPUB; USPAT; USOCR	OR	ON	2009/11/03 10:55
S22	2	S20 and ("pure-water" water aqueous)	US-PGPUB; USPAT; USOCR	OR	ON	2009/11/03 11:06
S23	0	S20 and period\$1	US-PGPUB; USPAT; USOCR	OR	ON	2009/11/03 11:10
S24	2	S20 and (rotat\$4 spin\$4)	US-PGPUB; USPAT; USOCR	OR	ON	2009/11/03 11:17
S25	2	S20 and dry\$3	US-PGPUB; USPAT; USOCR	OR	ON	2009/11/03 11:30
S26	2	("20020130106" "20030084925").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2009/11/03 14:01
S27	2	S26 and (reduc\$3 less lessen\$3 slow \$3 stop stopp\$3 off)	US-PGPUB; USPAT; USOCR	OR	ON	2009/11/03 14:01
S28	2	("20020130106" "20030084925").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2009/11/03 15:36
S29	2	S28 and rins\$3	US-PGPUB; USPAT; USOCR	OR	ON	2009/11/03 15:36
S30	2	S28 and dry\$3	US-PGPUB; USPAT; USOCR	OR	ON	2009/11/03 15:46
S31	1	"20070131256".pn.	US-PGPUB; USPAT; USOCR	OR	ON	2009/11/03 16:06
S32	1	S31 and faster same peripheral	US-PGPUB; USPAT; USOCR	OR	ON	2009/11/03 16:06
S33	2	("20020130106" "20030084925").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2009/11/03 16:08
S34	2	S33 and (reduc\$3 less lessen\$3 slow \$3 stop stopp\$3 off)	US-PGPUB; USPAT; USOCR	OR	ON	2009/11/03 16:08

S35	2	S33 and (increas\$3 more fast\$3)	US-PGPUB; USPAT; USOCR	OR	ON	2009/11/03 16:11
S36	2	S33 and ("3" arm\$1 moving move\$2 movement movable)	US-PGPUB; USPAT; USOCR	OR	ON	2009/11/03 16:14
S37	2	S28 and (nitrogen "n.sub.2")	US-PGPUB; USPAT; USOCR	OR	ON	2009/11/03 16:35
S38	1	S31 and ("10" same "15")	US-PGPUB; USPAT; USOCR	OR	ON	2009/11/03 16:51
S39	1	("5997653").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2009/11/03 16:56
S40	2	("20020130106" "20030084925").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2009/11/03 16:56
S41	7125	(substrate\$1 wafer\$1 semiconductor \$1 workpiece\$1) and (clean\$4 treat \$4 wash\$3) and ((rins\$3 "pure-water" water) same (mov\$3 advanc \$3 cross\$3 go goes going migrat\$3) same (out outward edge circumference)) and (((spin\$4 rotat \$3) and dry\$3) spin-dry\$3) and (film \$1 layer\$1)	US-PGPUB; USPAT	OR	ON	2009/11/03 16:56
S42	363	S41 and ((substrate\$1 wafer\$1 semiconductor\$1 workpiece\$1) same (clean\$4 treat\$4 wash\$3)) and ((rins \$3 "pure-water" water) with (mov\$3 advanc\$3 cross\$3 go goes going migrat\$3) with (out outward edge circumference)) and (((spin\$4 rotat \$3) and dry\$3) spin-dry\$3) same (film\$1 layer\$1))	US-PGPUB; USPAT	OR	ON	2009/11/03 16:56
S43	2353	(substrate wafer semiconductor workpiece) and (clean cleaning treat treating treatment wash washing) and ((rinse rinsing "pure-water" water) same (move moves moving moved advance advances advancing advanced cross crosses crossing across go goes going migrate migrating migrates migration) same (out outward edge circumference)) and (((spin spinning spun rotate rotation rotated rotating) and dry drying dried) "spin-dry" "spin-drying" "spin-dries") and (film layer)	USOCR	OR	ON	2009/11/03 16:56
S44	978	S43 and (nitrogen "n.sub.2")	USOCR	OR	ON	2009/11/03 16:56
S45	1343	S39 S40 S42 S44	US-PGPUB; USPAT; USOCR	OR	ON	2009/11/03 16:56
S46	418	S45 and ("10" ten "15" fifteen) same (mm millimet\$3) same (gas nitrogen "n.sub.2" gaseous)	US-PGPUB; USPAT; USOCR	OR	ON	2009/11/03 16:59
S47	102	S46 and ("10" ten "15" fifteen) near3 (mm millimet\$3) same (gas nitrogen "n.sub.2" gaseous)	US-PGPUB; USPAT; USOCR	OR	ON	2009/11/03 16:59

S48	94	S47 and (gas nitrogen "n.sub.2" gaseous) same (stop\$1 stopp\$3 less lessen\$3 decreas\$3 off slow\$3 reduc\$3)	US-PGPUB; USPAT; USOCR	OR	ON	2009/11/03 17:01
S49	11	S48 and (("10" ten "15" fifteen) near3 (mm millimet\$3)) same ((gas nitrogen "n.sub.2" gaseous) near5 (stop\$1 stopp\$3 less lessen\$3 decreas\$3 off slow\$3 reduc\$3))	US-PGPUB; USPAT; USOCR	OR	ON	2009/11/03 17:02

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